



A 94.2%-Peak-Efficiency 1.53A Direct-Battery-Hook-Up Hybrid Dickson Switched-Capacitor DC-DC Converter with Wide Continuous Conversion Ratio in 65nm CMOS

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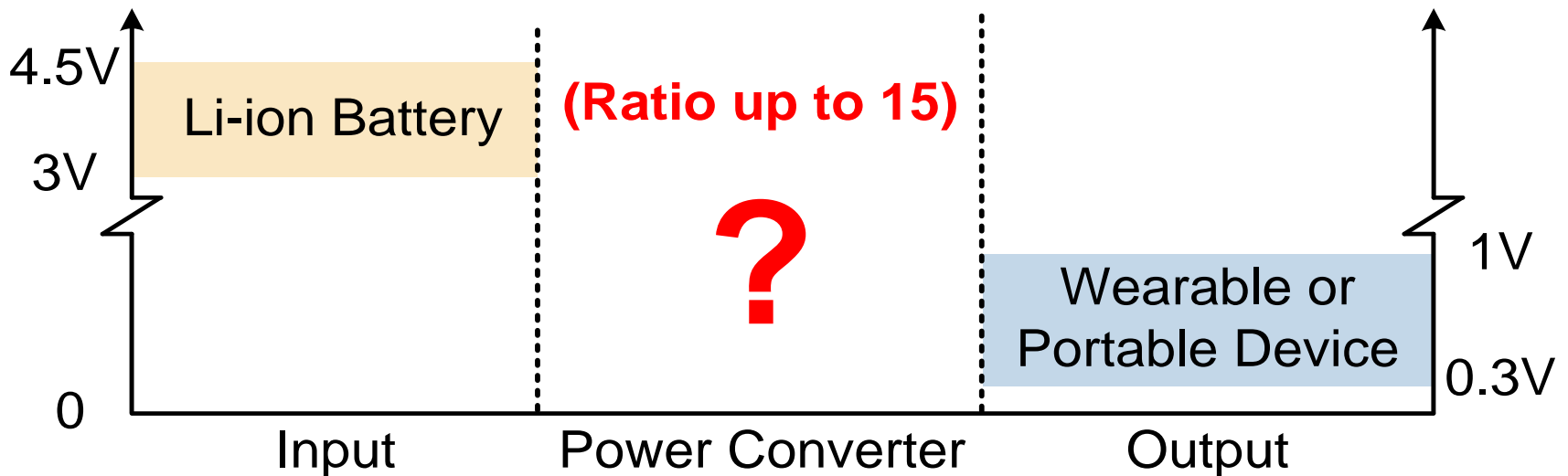
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Motivation

- Power converter requires

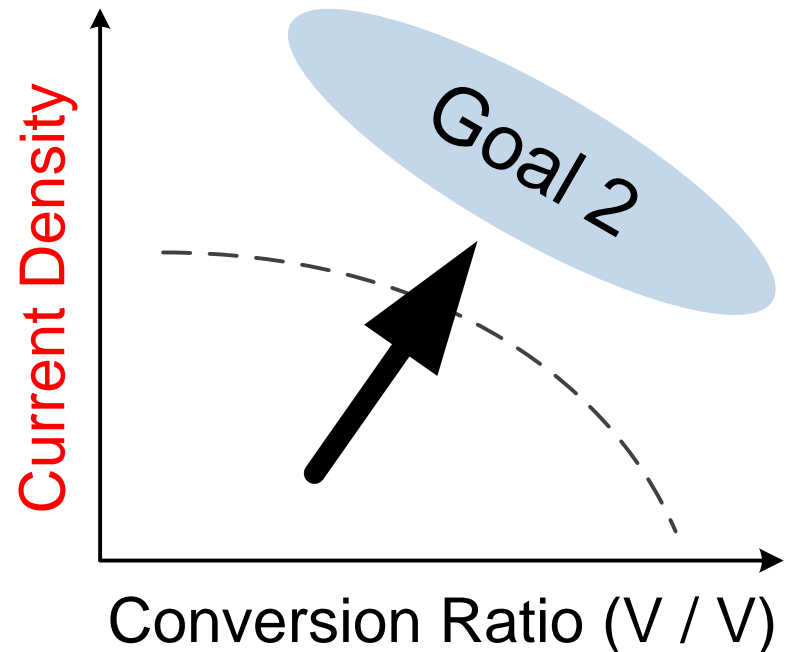
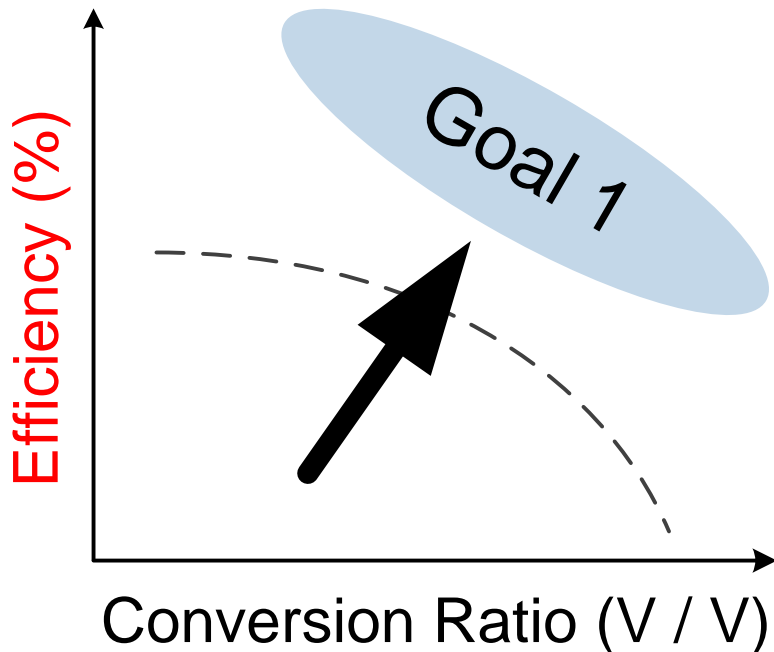
- High conversion ratio
- High current / power density
- High efficiency

WIDE-range
regulation



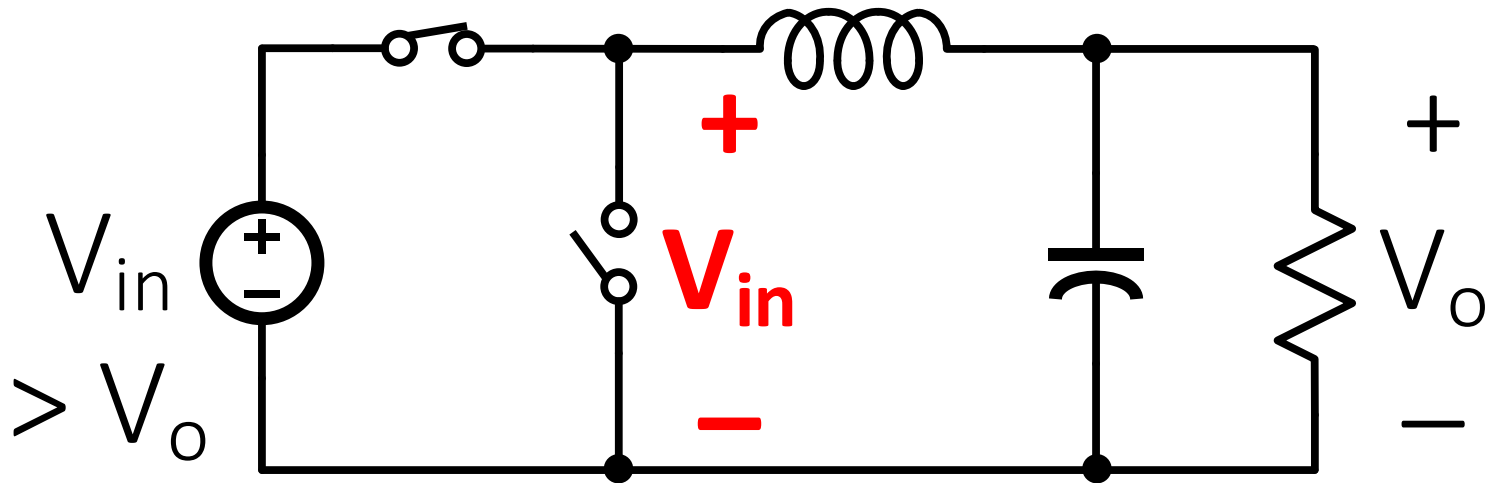
Performance Index

- Conventional SC converter
 - Goal 1 but only at some discrete high ratios
 - Prior arts addressed it using multiple stages but at the sacrifice of Goal 2



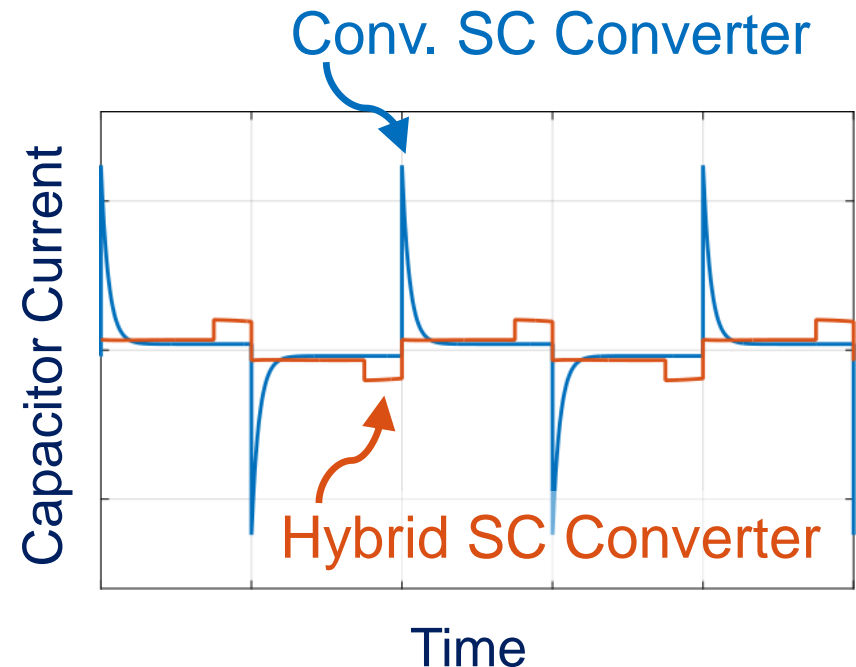
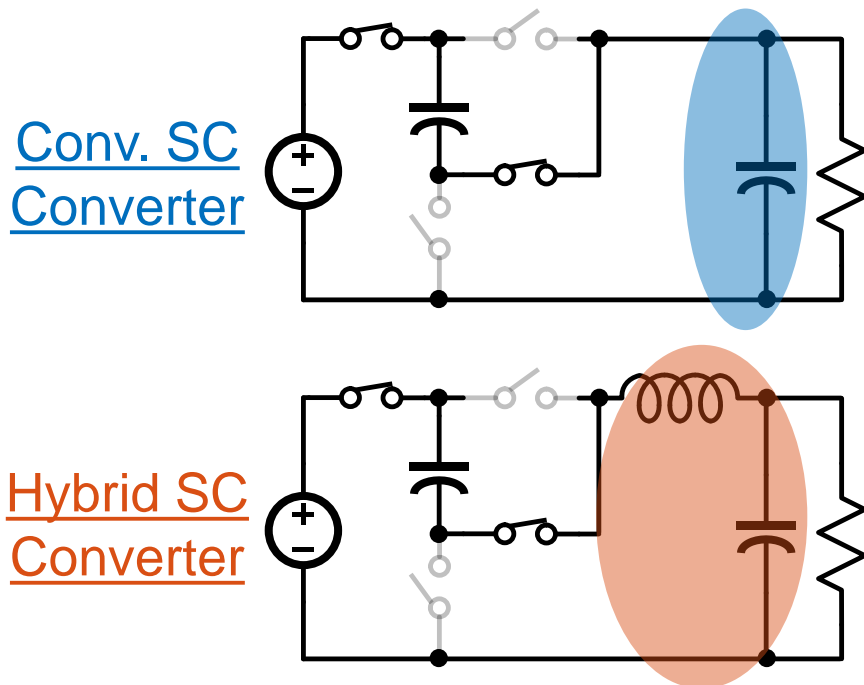
Performance Index

- Conventional buck converters
 - Hard to achieve Goals 1 and 2, due to the large device voltage stress relative to the output
 - High voltage rating: higher $R_{ds,on}$ per area



Hybrid SC Converter

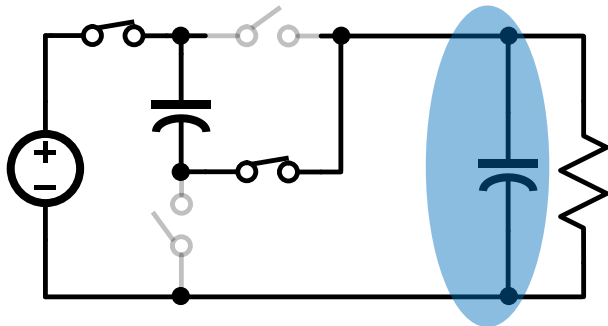
- No more charge redistribution loss
 - Reduces the RMS and peak capacitor current
 - Low R_o and independent of switching frequency



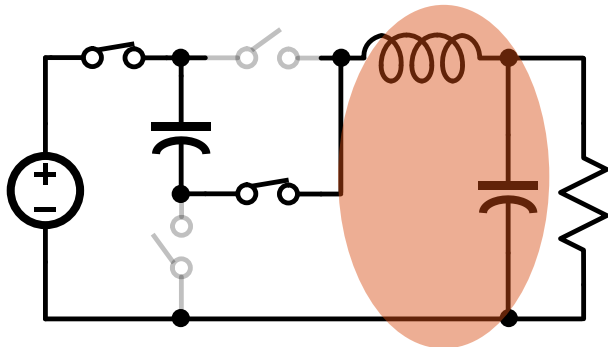
Hybrid SC Converter

- Efficiency improvement
 - Larger capacitors voltage ripple is allowed
 - Capacitor values can be reduced
 - f_{sw} can be lowered to reduce switching losses

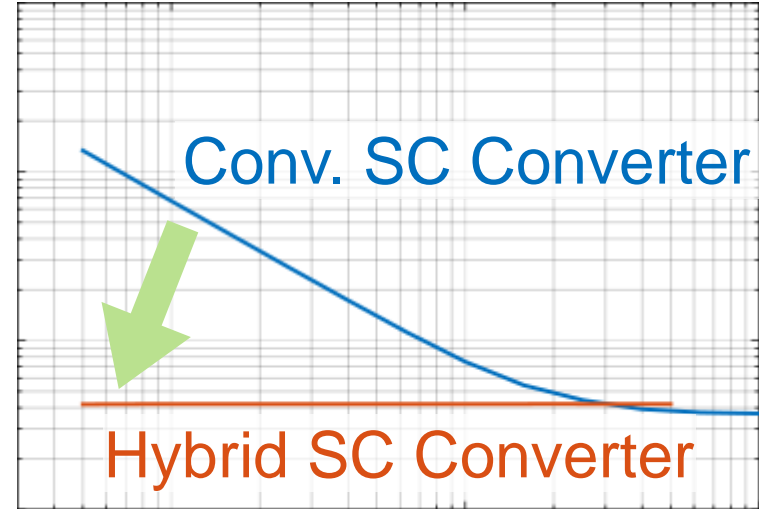
Conv. SC Converter



Hybrid SC Converter

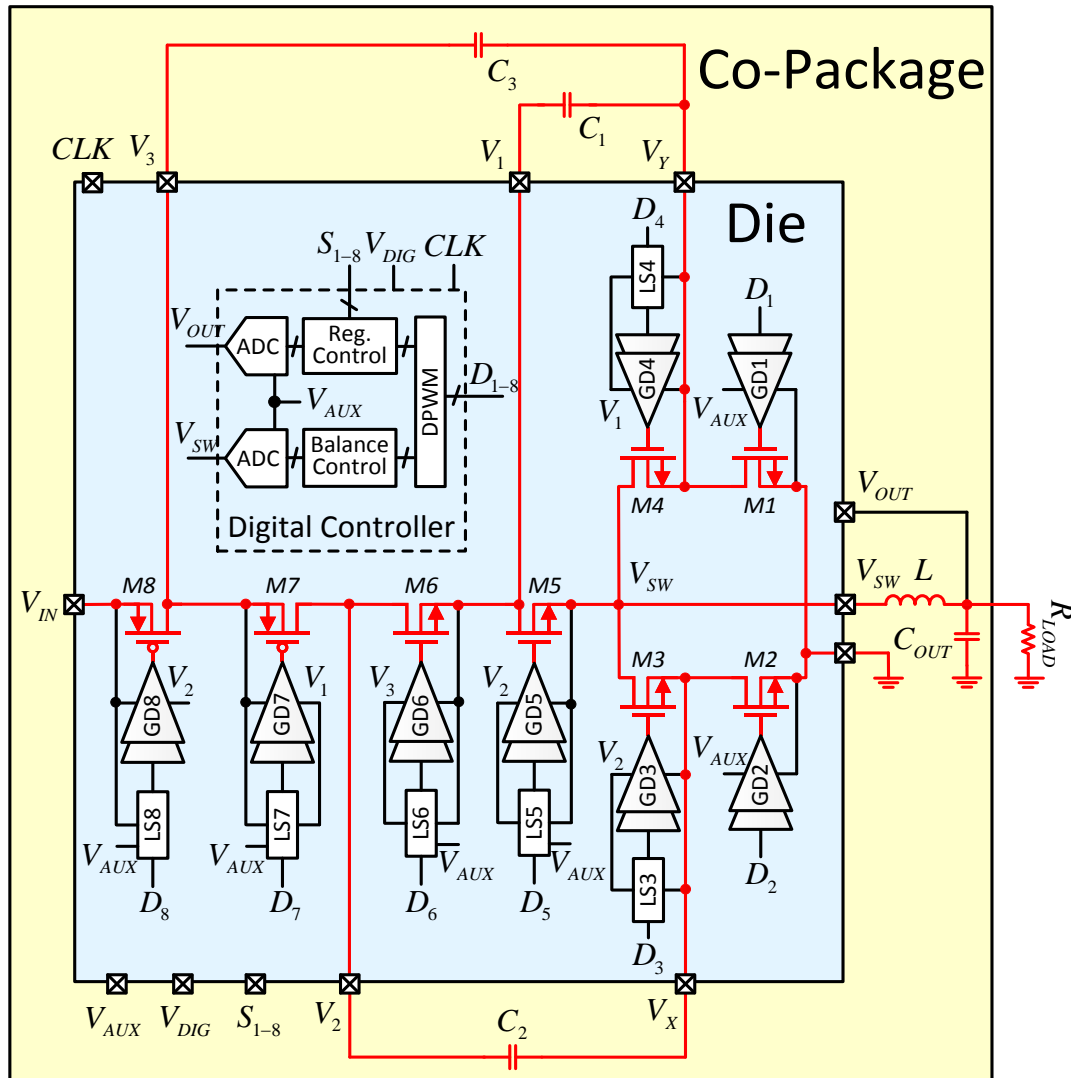


Output Impedance, R_o



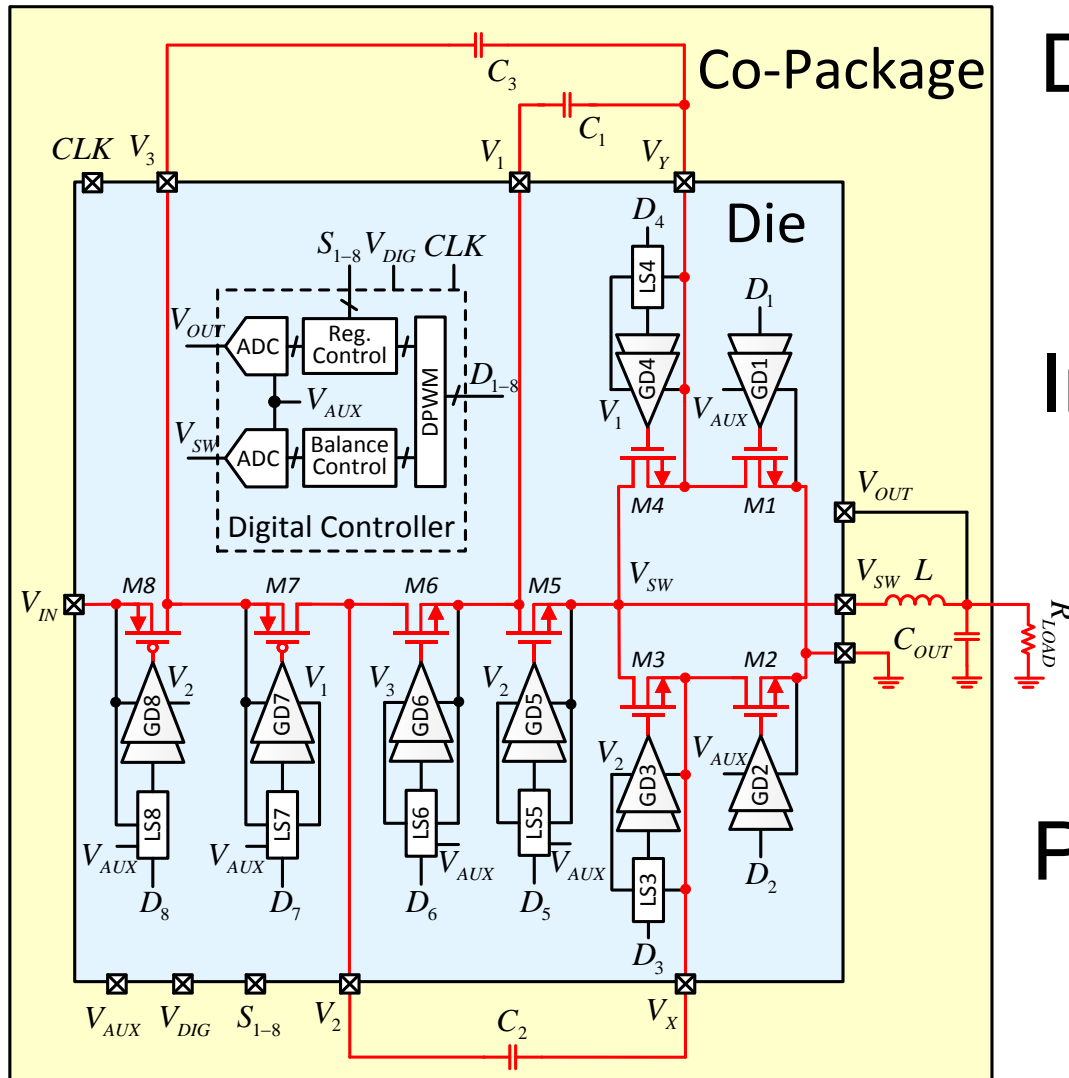
Switching Frequency

System Architecture



- Hybrid 4-to-1 Dickson converter
 - 8 power MOSFETs
 - 3 flying capacitors
 - 1 output capacitor
 - 1 inductor
- Gate driver (GD)
- Level shifter (LS)
- V_{out} regulation
- Cap. balancing

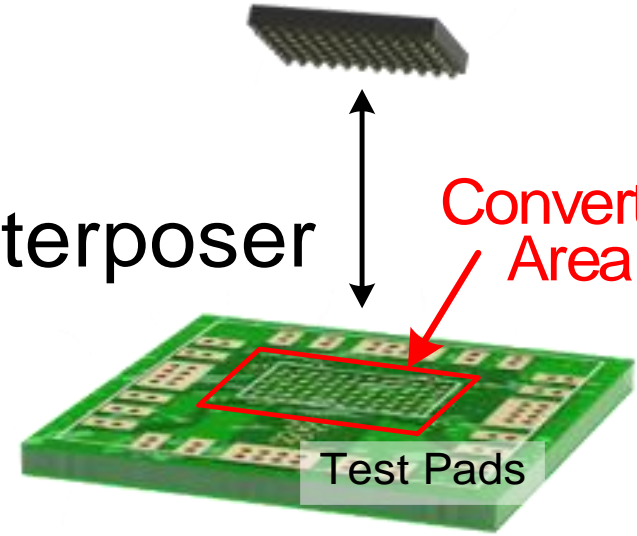
Package – High Current Density



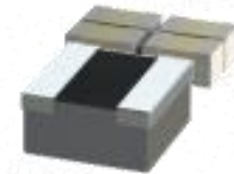
Die (Flipchip)

Interposer

Converter Area

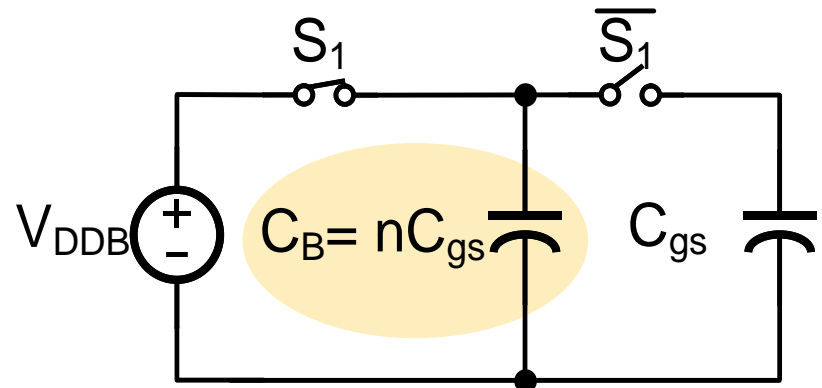
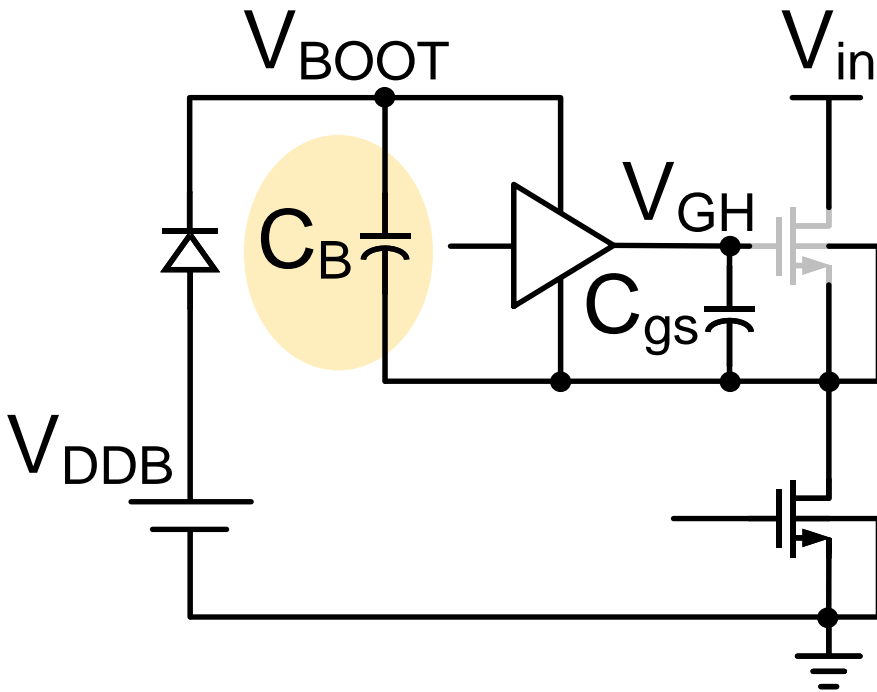


Passives



Capacitor Area Reduction

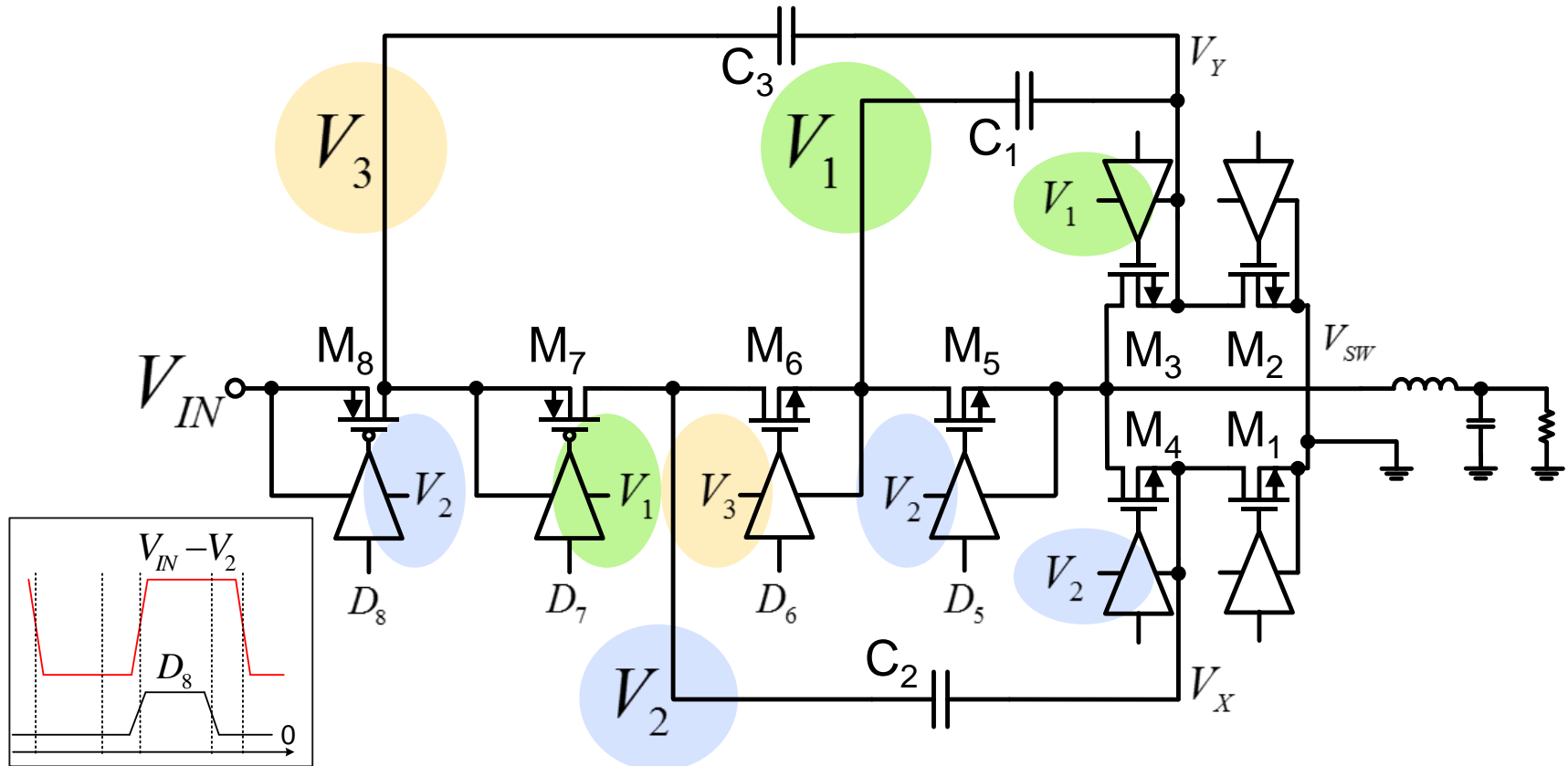
- Conventional boot-strap GD consumes considerable on-die C_B , e.g. $C_B = 10C_{gs}$
- Low V_{gs} increases $R_{ds,on}$ per area



$$\frac{V_{gs}}{V_{DDB}} = 1 - \left(\frac{1}{n+1} \right)$$

Voltage Borrowing Technique

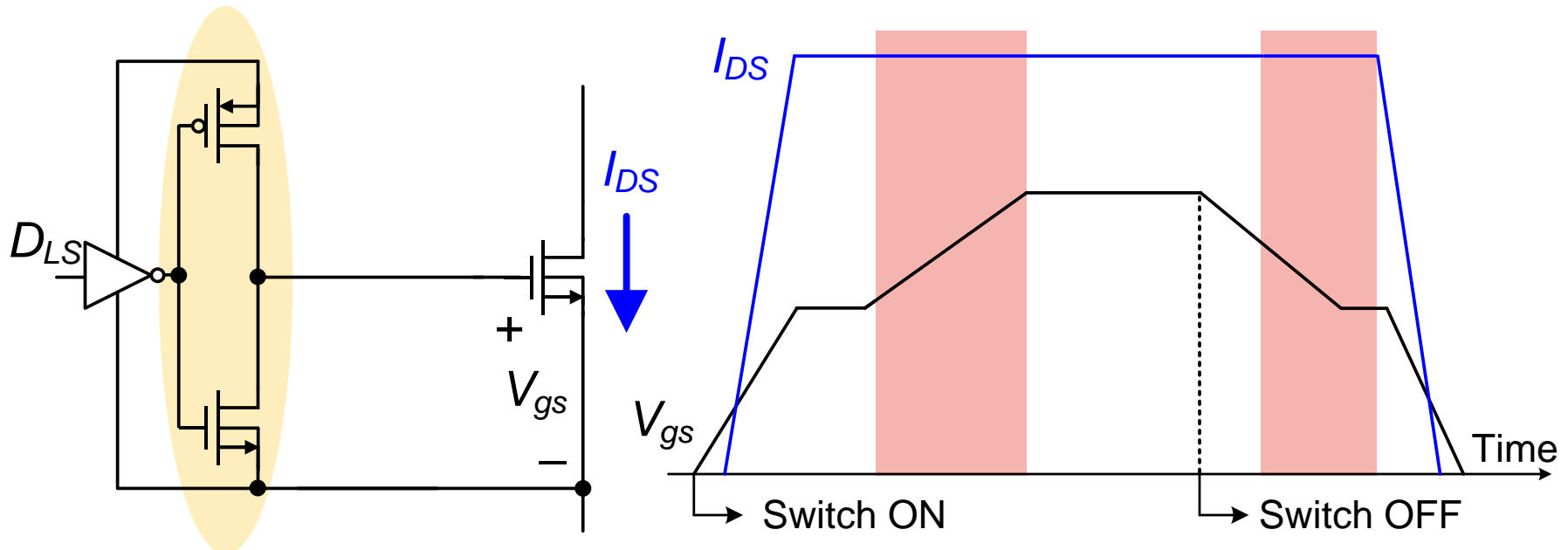
- Powered by existing flying capacitors
 - No extra capacitor needed
 - No extra voltage supply circuit needed



Ringing Reduction

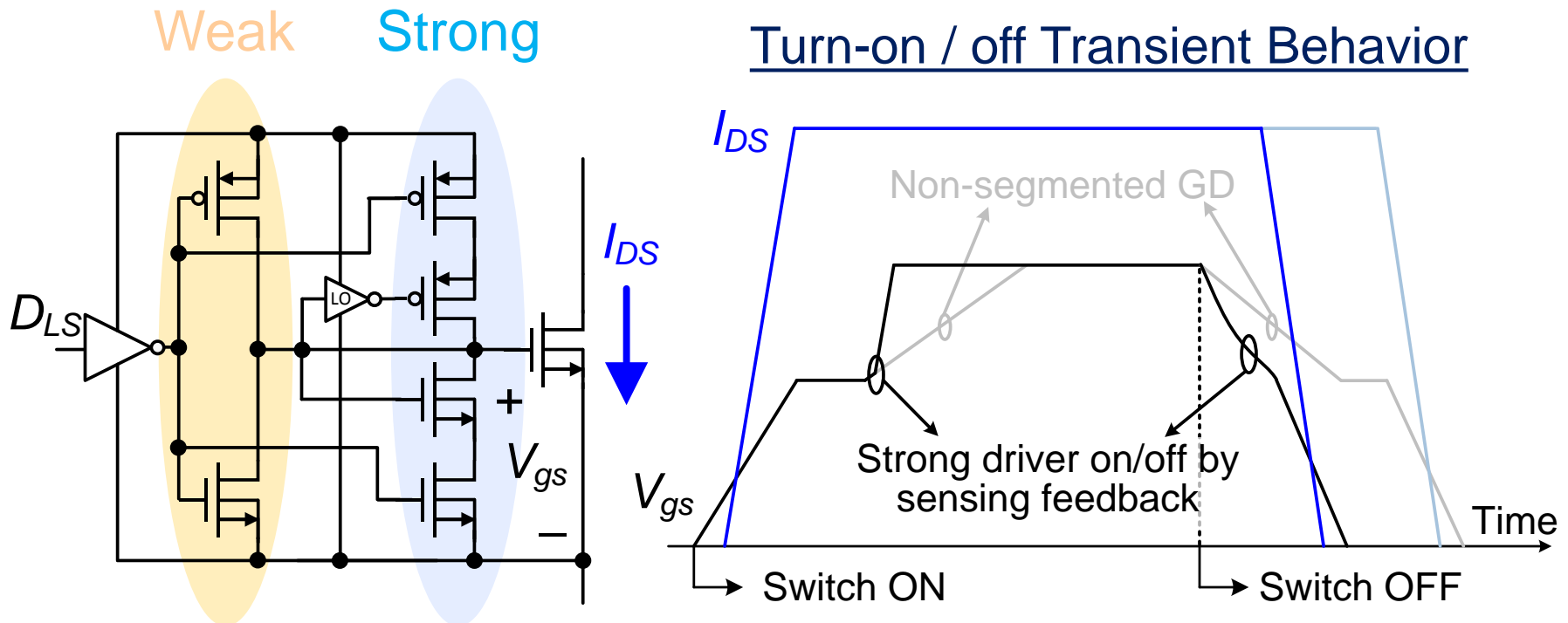
- Too fast transition: large ringing
- Too slow transition: low efficiency
 - Low V_{gs} increases conduction loss
 - Worse if running at higher switching frequency

Weak



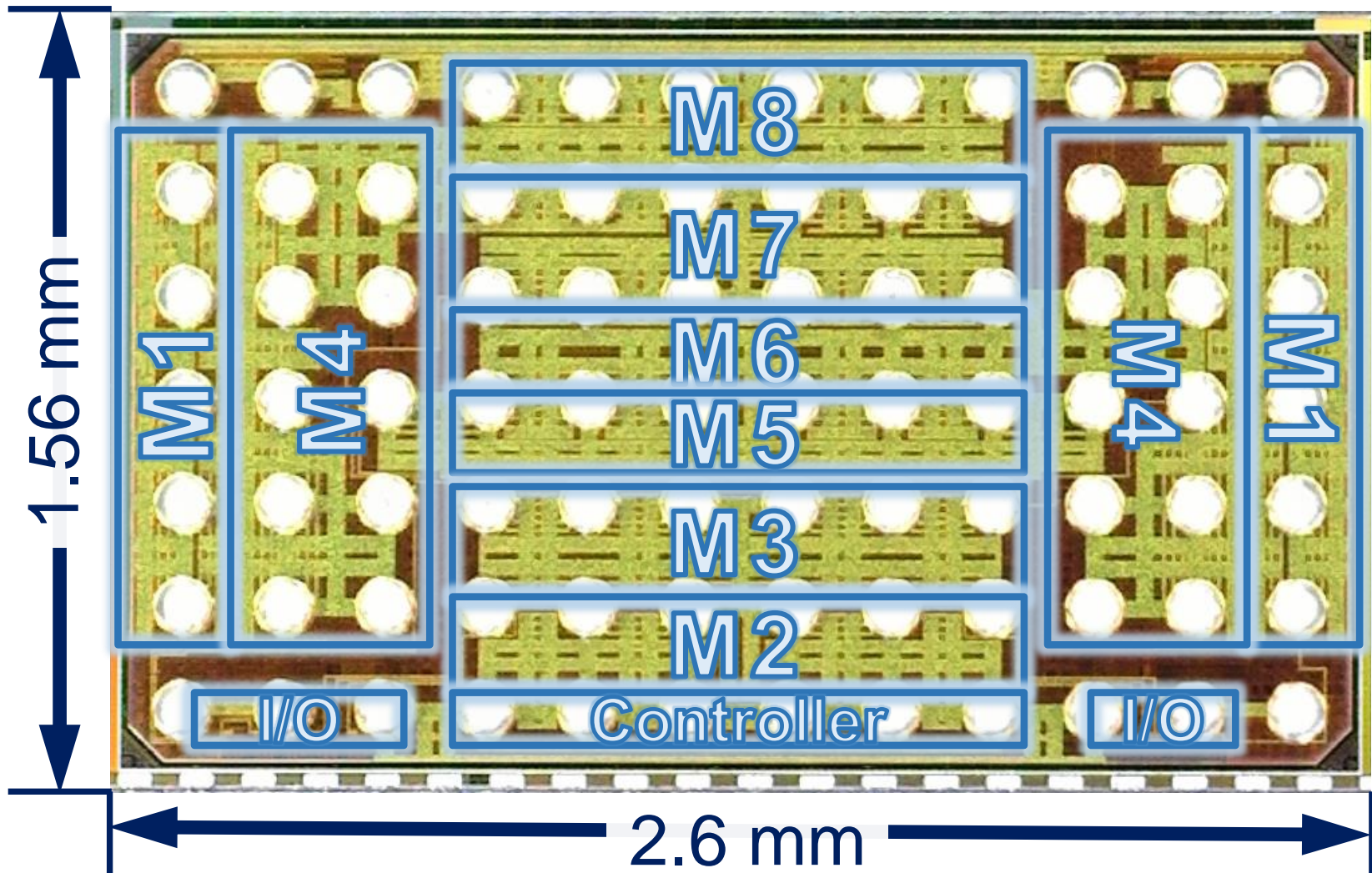
Segmented Gate Driver

- Ringing reduction w/o sacrifice of efficiency
 - Weak driver first slows down the transition
 - Strong driver then raises V_{GS} at a faster rate so that the switch reaches the low $R_{ds,on}$ sooner



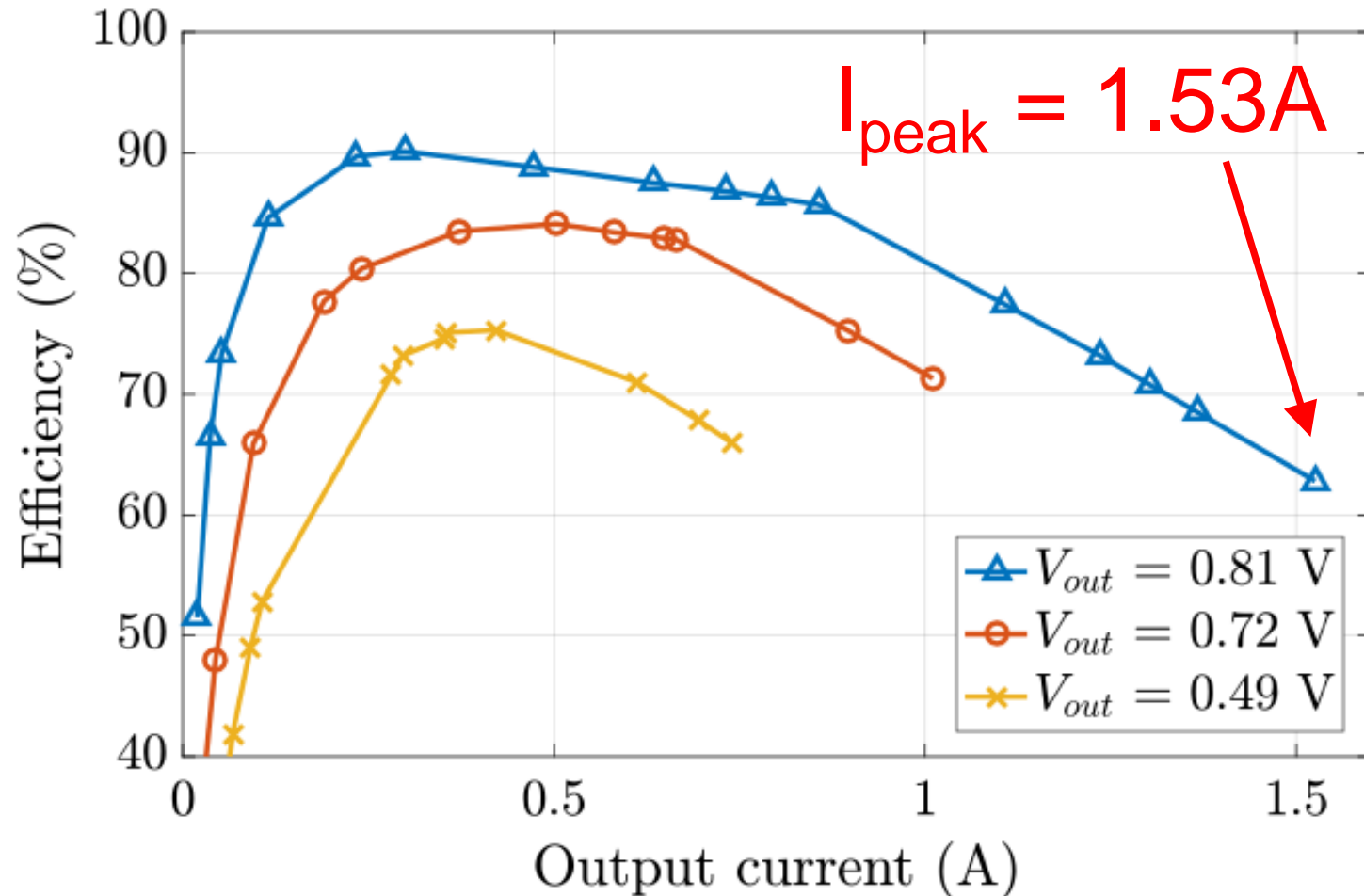
Die Micrograph

- 65nm bulk CMOS process



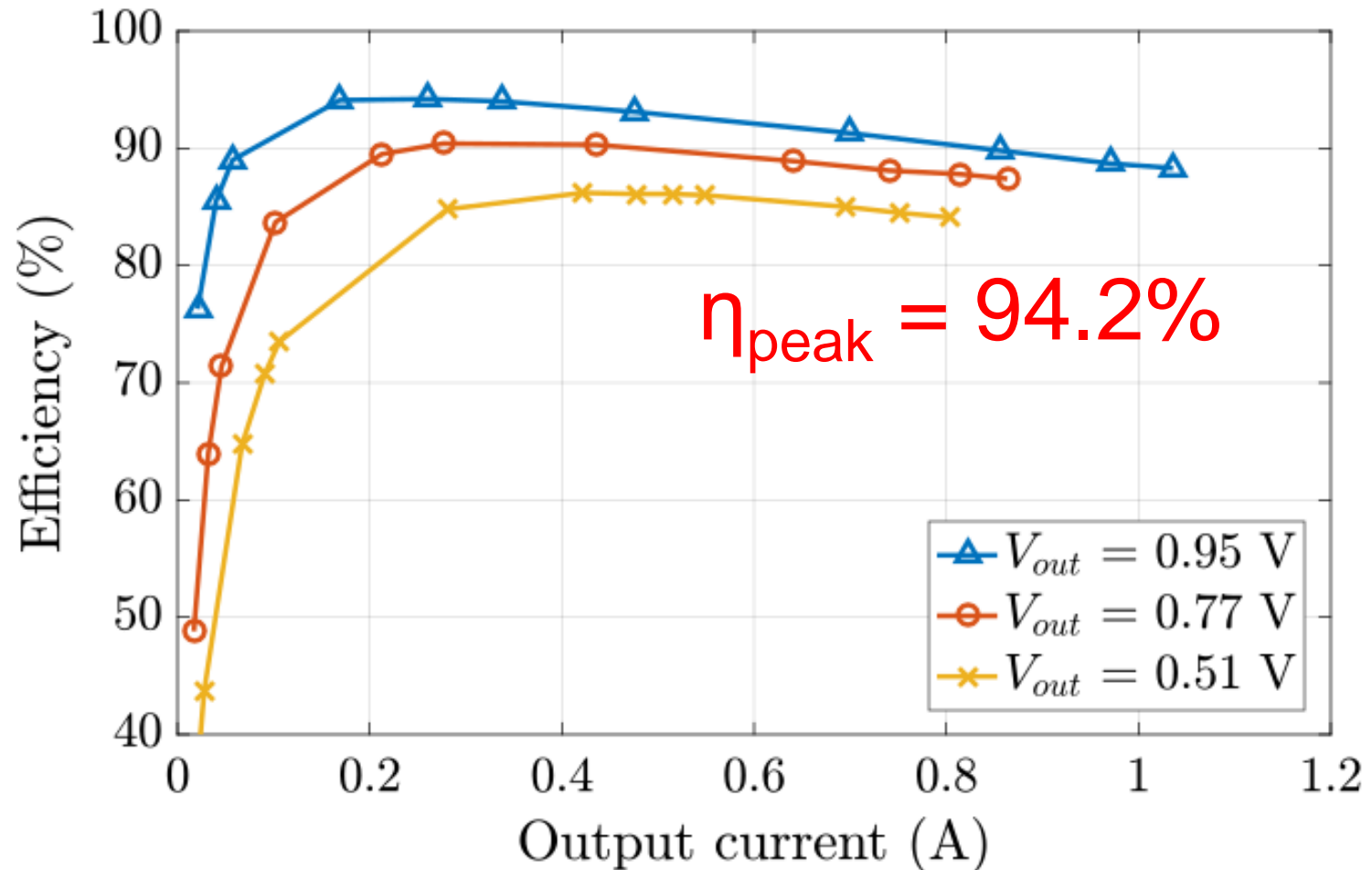
Measured Efficiency

- $V_{in} = 4.2 \text{ V}$, $L = 180 \text{ nH}$, $\text{DCR} = 24 \text{ m}\Omega$

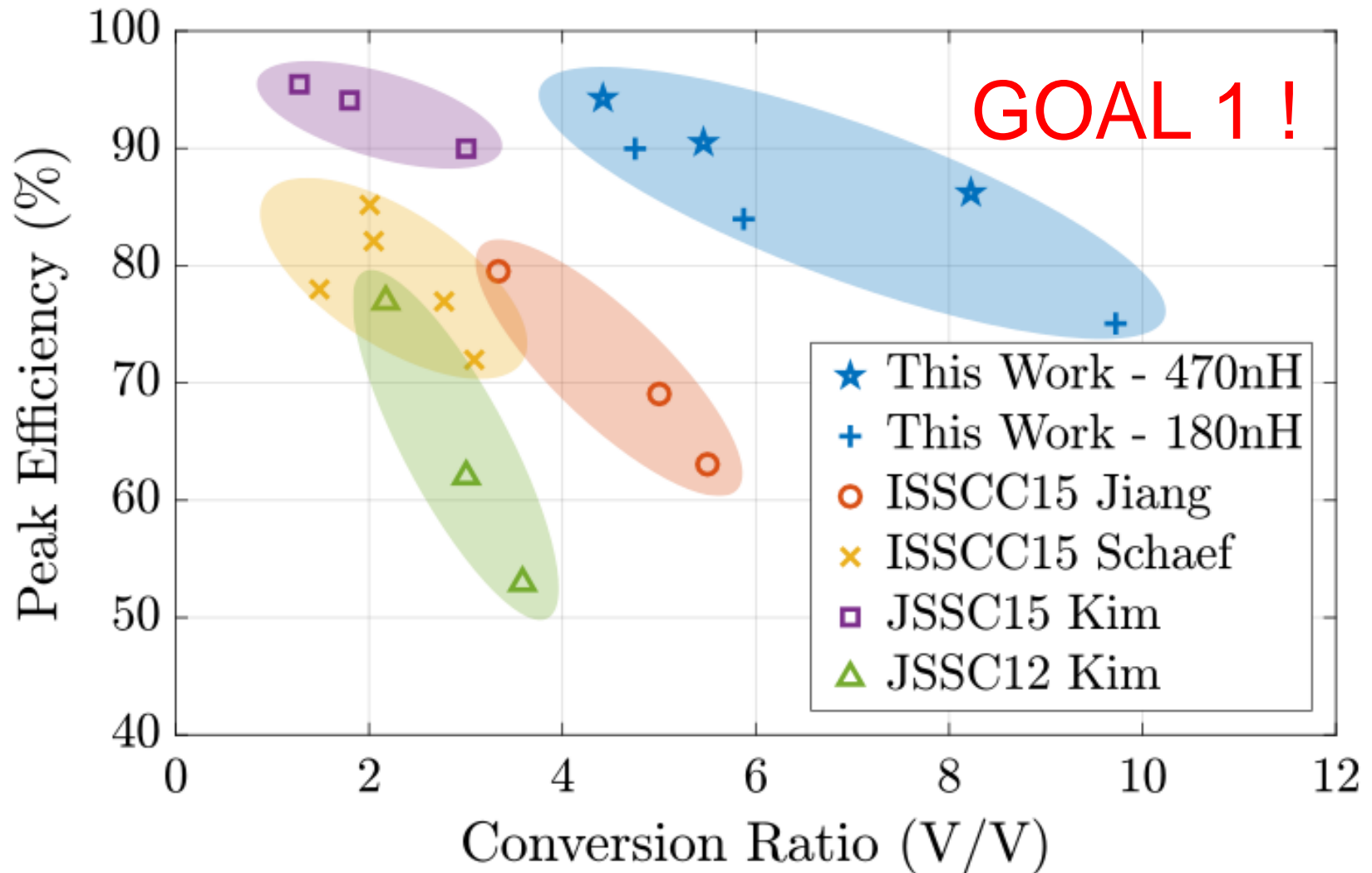


Measured Efficiency

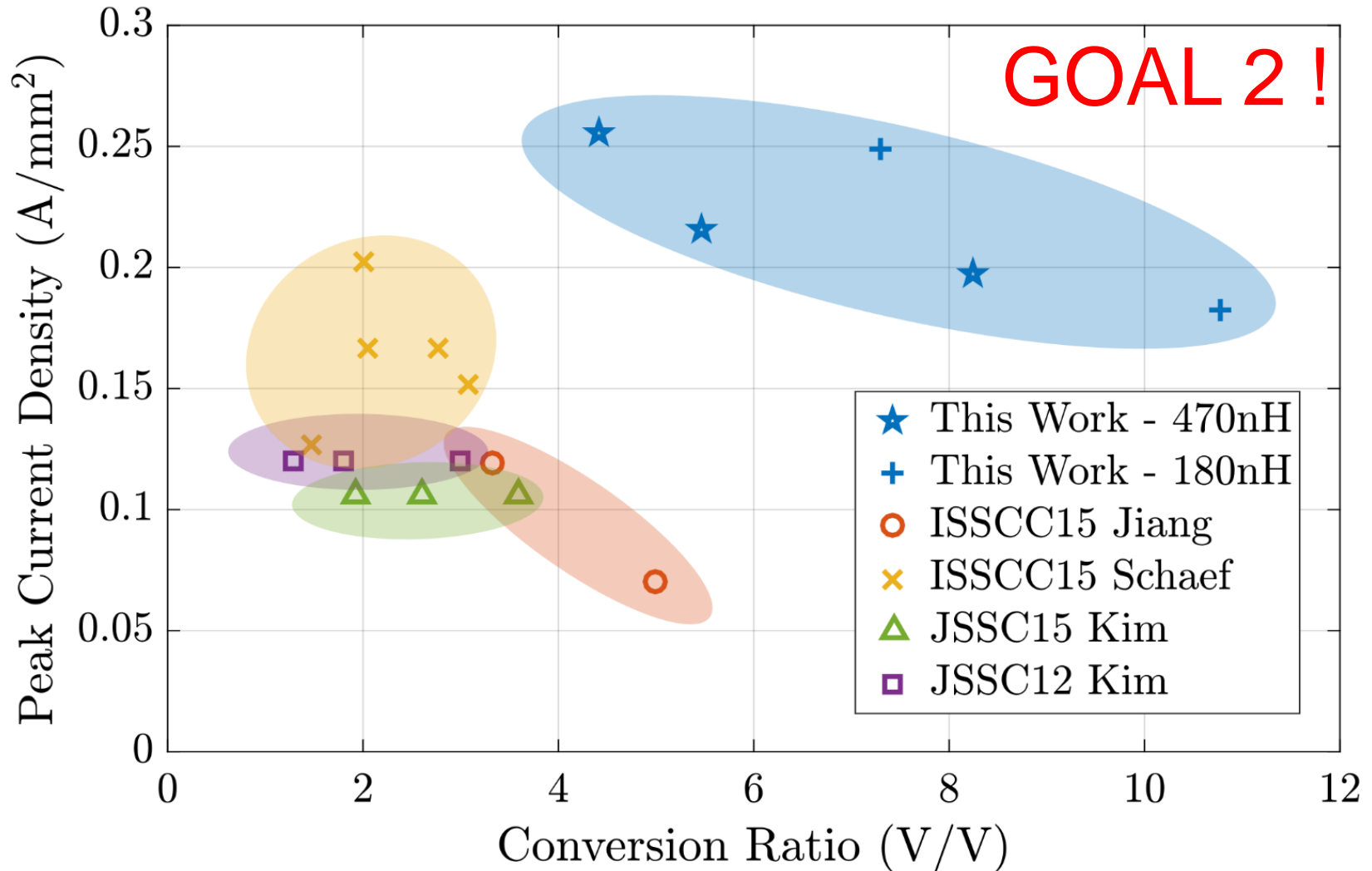
- $V_{in} = 4.2 \text{ V}$, $L = 470 \text{ nH}$, $\text{DCR} = 8 \text{ m}\Omega$



Performance Comparison



Performance Comparison



Conclusion

- First CMOS implementation of a hybrid Dickson SC converter
 - High power density and efficiency for high step-down
 - Good for low-voltage loads powered by Li-ion batteries
- Capacitor area reduction
 - Floating gate driver and level shifter are powered by the flying capacitors themselves
- Ringing reduction w/o sacrifice of efficiency
 - Segmented gate driver uses both slow and fast drivers

Acknowledgements

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Questions ?

Voltage Borrowing Technique

- Selected voltage

- High enough to turn on switches with low $R_{ds,on}$
- Within switch voltage ratings

